

**ECE 733**  
**Final Spring 2006**

This test is open book, open notes. Computers are NOT allowed (calculators are). You have 75 minutes. Turn in answers on your own paper.

**Question 1**

Consider the following cross-section for an interconnect circuit:

- Line width = 10  $\mu\text{m}$ ; Line thickness = 2  $\mu\text{m}$
- Line material: Aluminum ( $\rho = 4.3\text{E-}8 \Omega\cdot\text{m}$ )
- Dielectric material : BCB.  $\epsilon_r=2.7$ ;  $\tan \delta = 0.0008$
- $\mu = 4\pi\text{E-}7$  (Magnetic permeability)
- $Z_0= 50 \text{ Ohm}$

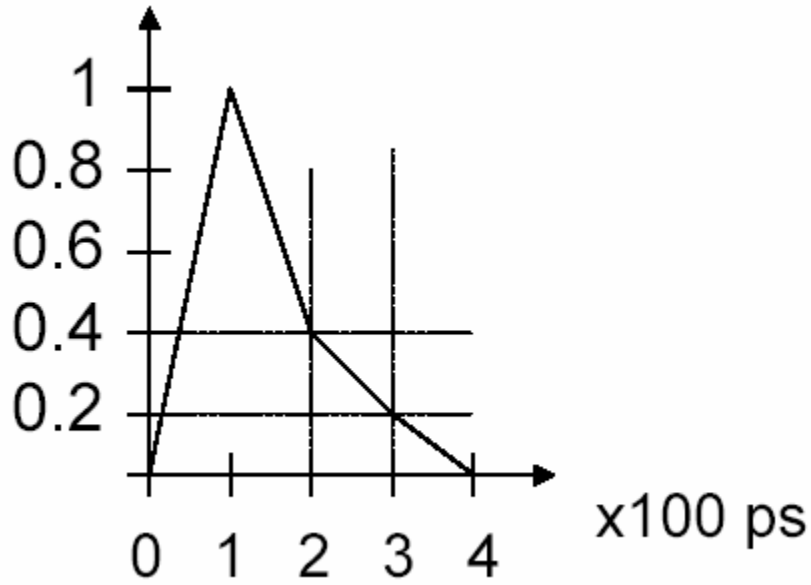
(a) At what frequency is the skin-depth half of the conductor thickness? [2 points]

(b) At what frequency does the attenuation due to the loss tangent exceed the attenuation due to the skin effect? [3 points]

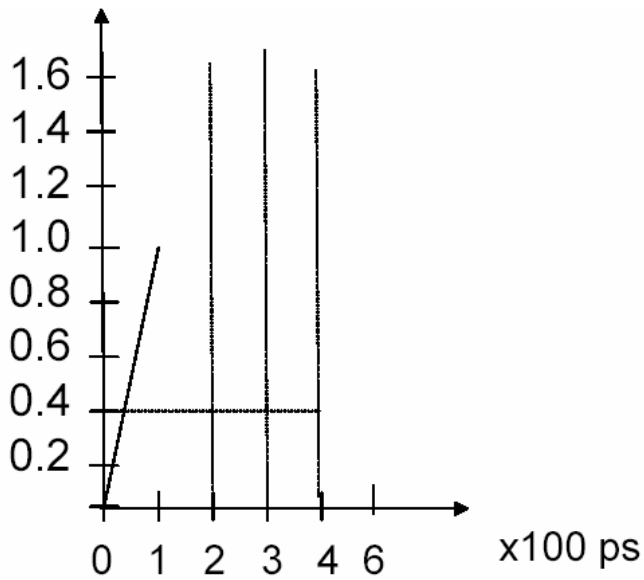
(c) Would you get the best Bit Error Rate by using PAM-2 or PAM-4 as your signaling scheme on this line? Carefully explain your answer. [2 points]

**Question 2**

Consider an interconnect circuit with the following pulse response to a 010 input operating at 10 Gbps.

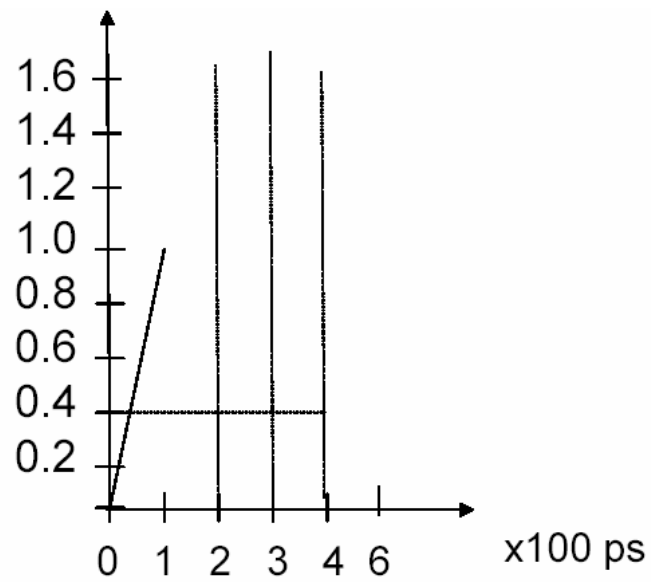


- (a) Based on this waveform, predict the waveform for a 0110 signal operating at 10 Gbps, as it would appear at the end of the same line. [4 points]



(b) How many taps (i.e. how many flip-flop delays) would you use in a pre-emphasis filter, and what are appropriate tap weights. [3 points]

(c) Draw the waveform at the end of the line for a 0110 signal operating at 10 Gbps, as produced by the driver with the filter. [2 points]



**Question 3**

Consider the 8T cell, considered in the distributed paper, and described below:

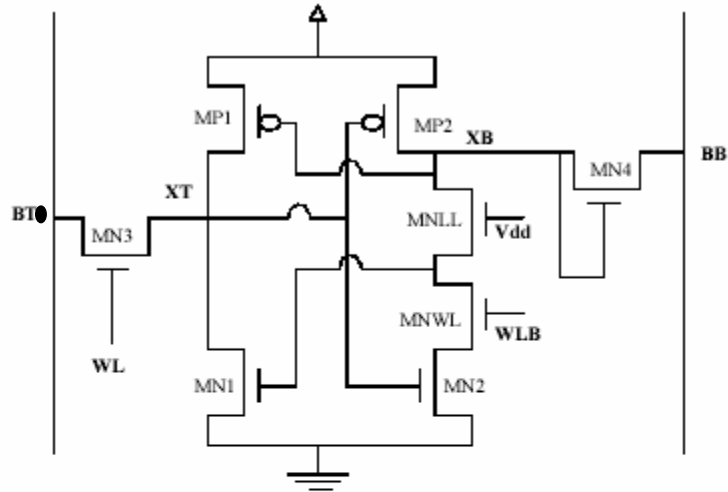


Figure 2. 8T SRAM Cell

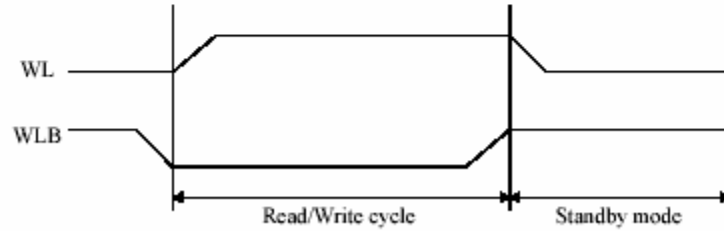


Figure 3. Timing Diagram

Please answer the following questions:

- (a) What are the constraints, if any, on the relative sizes of MN1 and MN3 to read a “0” stored at XT without upsetting the state of the memory? Clearly justify your answer. [2 points]
  
- (b) For the SRAM to work correctly, it needs to ensure that when reading a stored “1”, then  $(BT, BB) = (1, 0)$  must be met, and for reading a stored “0”, that  $(BT, BB) = (0, 1)$  must be met. What potential issues do you see driving  $BB \rightarrow 0$  if XB is low? Thus, how should the column “load” circuits be redesigned to ensure correct operation? [2 points]